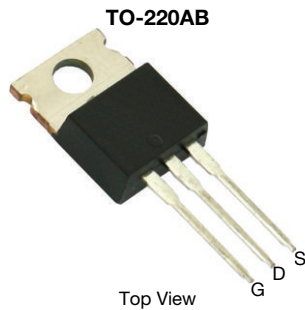


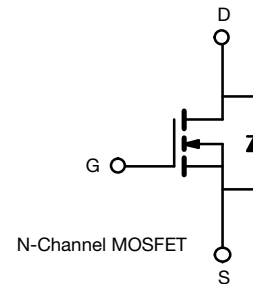
Automotive N-Channel 60 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified ^d
- 100 % R_G and UIS tested
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


PRODUCT SUMMARY	
V _{DS} (V)	60
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0035
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.0040
I _D (A)	120
Configuration	Single
Package	TO-220

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	60	V	
Gate-source voltage	V _{GS}	± 20		
Continuous drain current	I _D	T _C = 25 °C ^a	120	A
		T _C = 125 °C	102	
Continuous source current (diode conduction) ^a	I _S	120		
Pulsed drain current ^b	I _{DM}	480		
Single pulse avalanche current	I _{AS}	L = 0.1 mH	100	
Single pulse avalanche energy			E _{AS}	
Maximum power dissipation ^b	P _D	T _C = 25 °C	250	W
		T _C = 125 °C	83	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient	R _{thJA}	40	°C/W	
Junction-to-case (drain)	R _{thJC}	0.6		

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	900	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.0025	0.0035	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0064	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0080	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0028	0.0040	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	190	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	11 755	14 700	pF
Output capacitance	C _{oss}			-	1112	1400	
Reverse transfer capacitance	C _{rss}			-	481	605	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 110 A	-	220	330	nC
Gate-source charge ^c	Q _{gs}			-	35	-	
Gate-drain charge ^c	Q _{gd}			-	35	-	
Gate resistance	R _g	f = 1 MHz		0.6	1.3	2	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.27 Ω I _D ≅ 110 A, V _{GEN} = 10 V, R _g = 2.5 Ω		-	19	29	ns
Rise time ^c	t _r			-	23	35	
Turn-off delay time ^c	t _{d(off)}			-	83	125	
Fall time ^c	t _f			-	35	53	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	480	A
Forward voltage	V _{SD}	I _F = 50 A, V _{GS} = 0		-	0.8	1.5	V

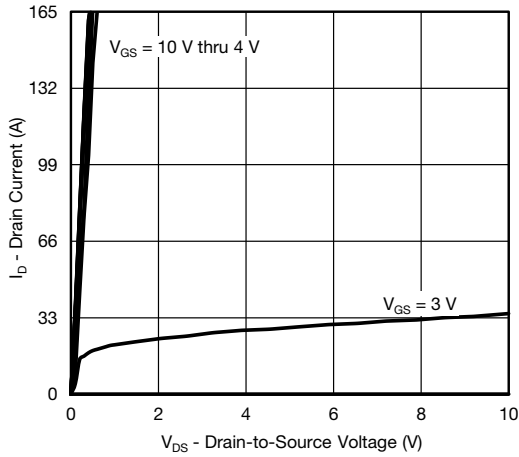
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

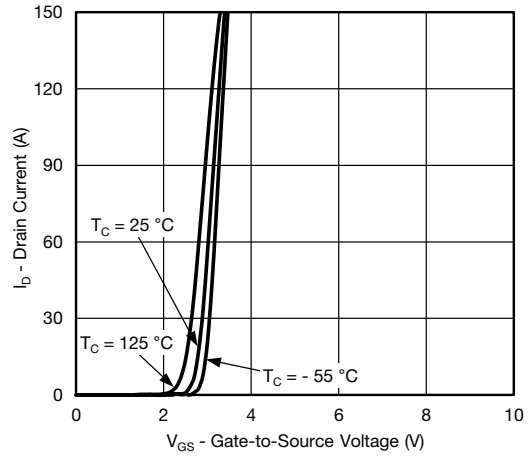
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.



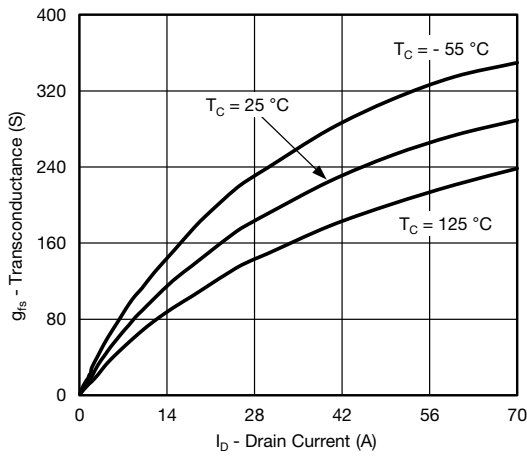
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



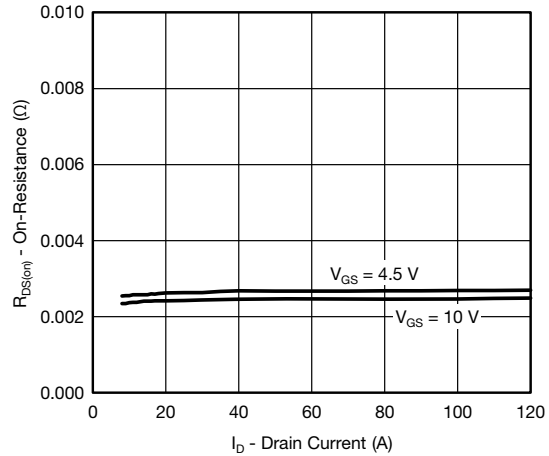
Output Characteristics



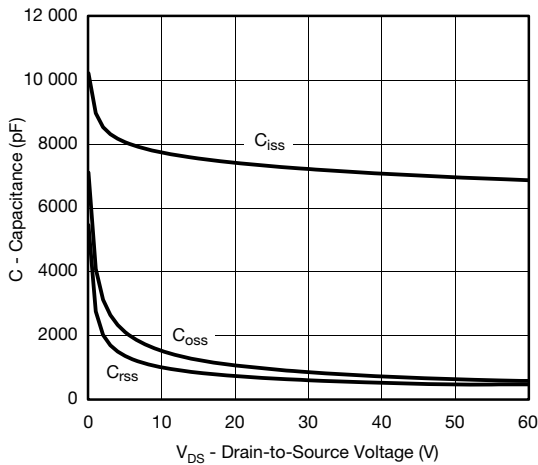
Transfer Characteristics



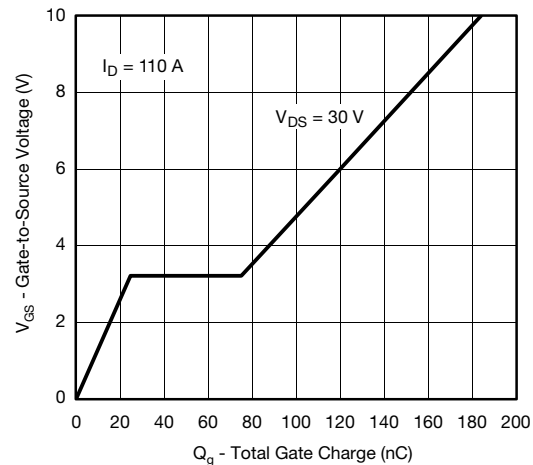
Transconductance



On-Resistance vs. Drain Current



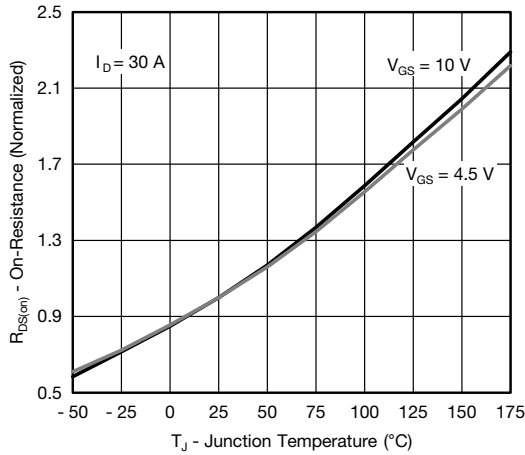
Capacitance



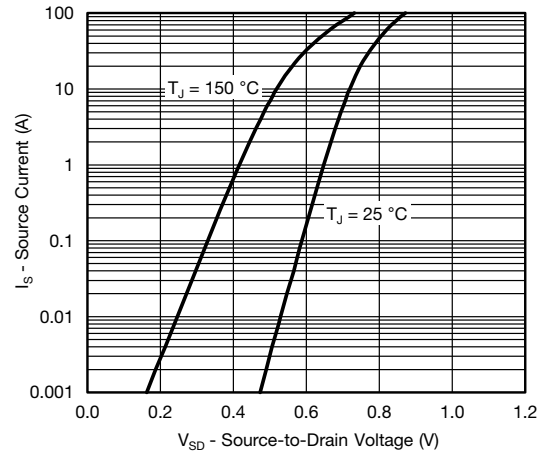
Gate Charge



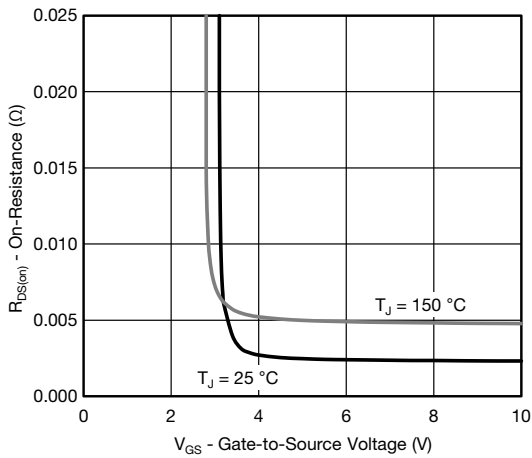
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



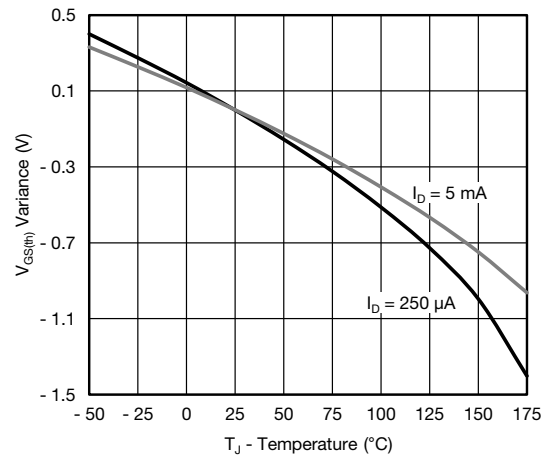
On-Resistance vs. Junction Temperature



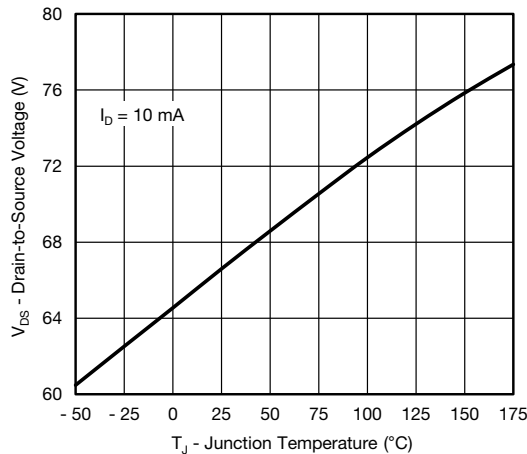
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



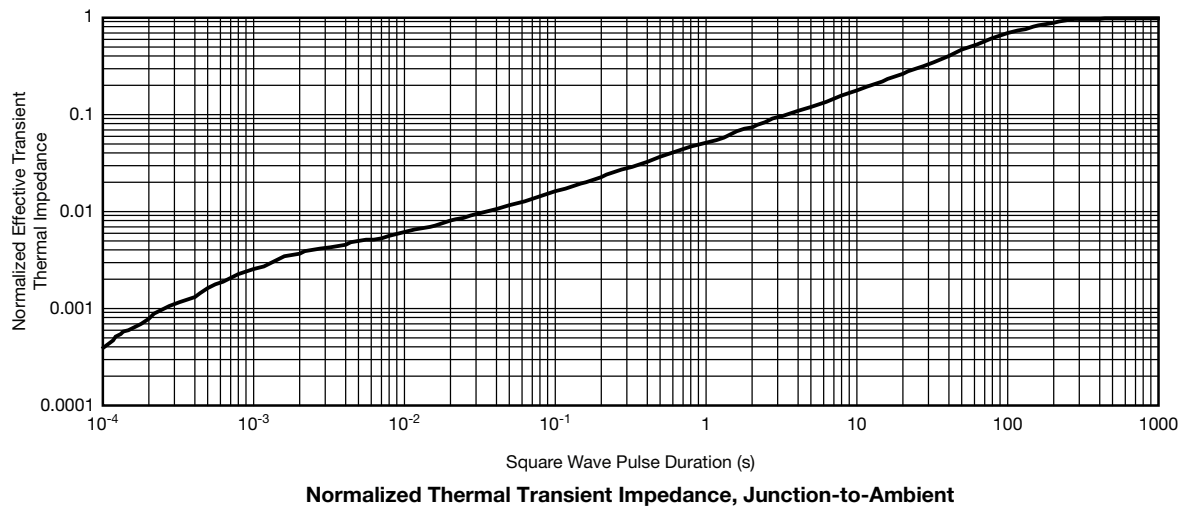
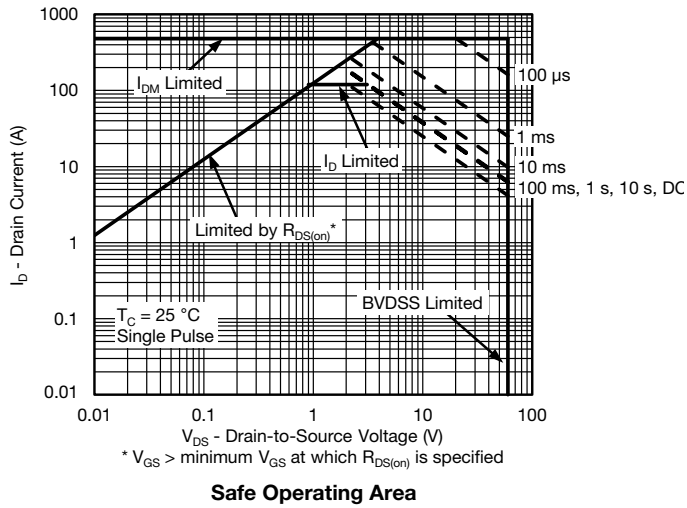
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

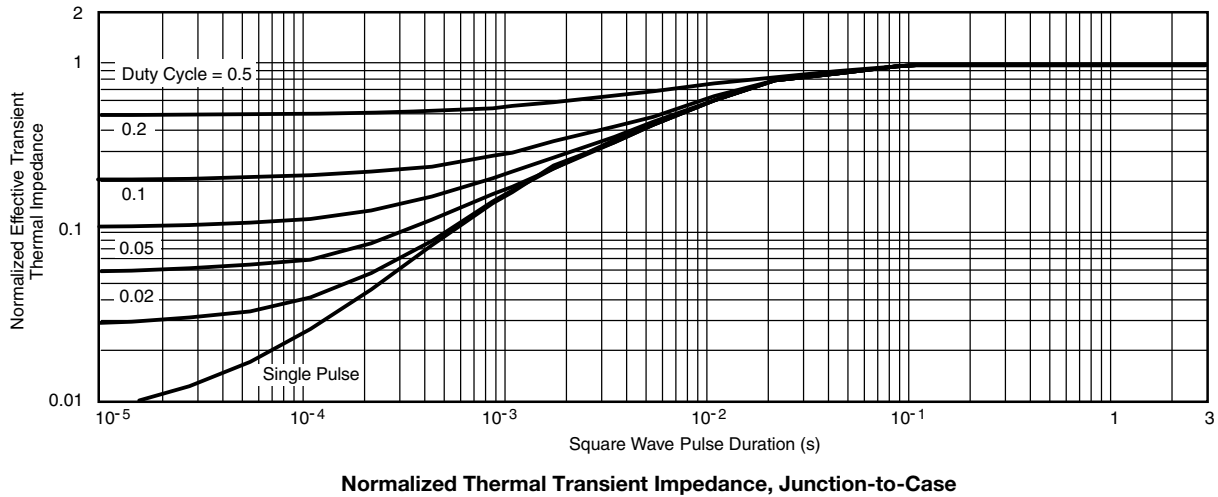


THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



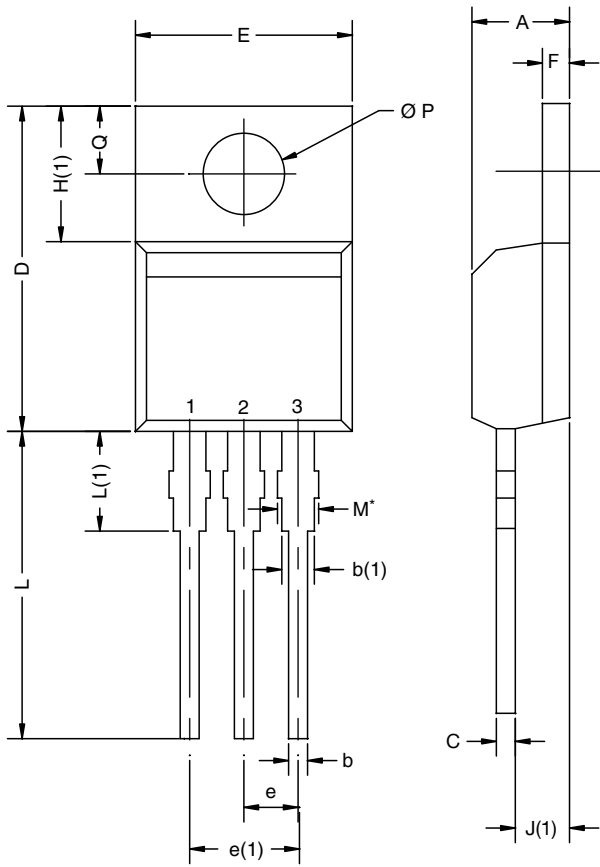
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-220AB

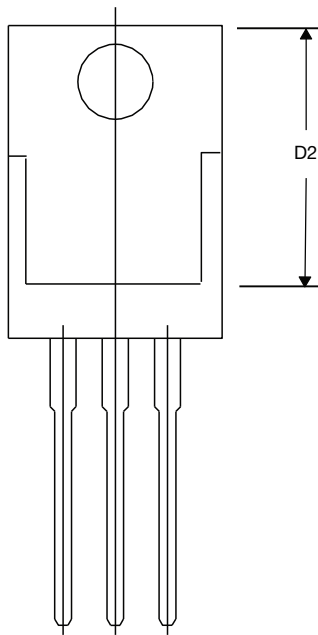


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14
DWG: 5471

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM





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